BC212B

Amplifier Transistors

PNP Silicon

Features

• These are Pb-Free Devices*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO}	-50	Vdc
Collector-Base Voltage	V _{CBO}	-60	Vdc
Emitter-Base Voltage	V _{EBO}	-5.0	Vdc
Collector Current - Continuous	Ic	-100	mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	P _D	350 2.8	mW mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	1.0 8.0	W mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS

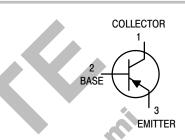
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	357	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	125	°C/W

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended , str. ereliabili Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

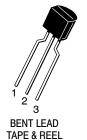


ON Semiconductor®

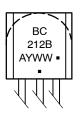
http://onsemi.com







MARKING DIAGRAM



= Assembly Location

= Year WW = Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
BC212BG	TO-92 (Pb-Free)	5000 Units / Bulk
BC212BRL1G	TO-92 (Pb-Free)	2000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

BC212B

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
Collector - Emitter Breakdown Voltage	V _{(BR)CEO}	-50	-	-	Vdc
Collector - Base Breakdown Voltage	V _{(BR)CBO}	-60	-	-	Vdc
Emitter – Base Breakdown Voltage	V _{(BR)EBO}	-5	-	-	Vdc
Collector-Emitter Leakage Current	I _{CBO}	_	-	-15	nAdc
Emitter-Base Leakage Current	I _{EBO}	-	-	-15	nAdc
ON CHARACTERISTICS	•	•	•	•	•
DC Current Gain ($I_C = -10 \mu Adc$, $V_{CE} = -5.0 Vdc$)	h _{FE}	40	-	_	-
$(I_C = -2.0 \text{ mAdc}, V_{CE} = -5.0 \text{ Vdc})$		60	_	_	
(I _C = -100 mAdc, V _{CE} = -5.0 Vdc) (Note 1)			120	_	
Collector – Emitter Saturation Voltage ($I_C = -10$ mAdc, $I_B = -0.5$ mAdc) ($I_C = -100$ mAdc, $I_B = -5.0$ mAdc) (Note 1)	V _{CE(sat)}	-	-0.10 -0.25	_ -0.6	Vdc
Base – Emitter Saturation Voltage (I _C = -100 mAdc, I _B = -5.0 mAdc)	V _{BE(sat)}	-	-1.0	-1.4	Vdc
Base–Emitter On Voltage (I _C = -2.0 mAdc, V _{CE} = -5.0 Vdc)	V _{BE(on)}	-0.6	-0.62	-0.72	Vdc
DYNAMIC CHARACTERISTICS					1
Current – Gain – Bandwidth Product (I _C = –10 mAdc, V _{CE} = –5.0 Vdc, f = 100 mHz)	f _T	- 1	280	_	MHz
Common-Base Output Capacitance (V _{CB} = -10 Vdc, I _C = 0, f = 1.0 mHz)	C _{ob}	COL	-	6.0	pF
Noise Figure (I _C = -0.2 mAdc, V _{CE} = -5.0 Vdc, R _S = 2.0 k Ω , f = 1.0 kHz, f = 200 Hz)	NF	-	-	10	dB
Small–Signal Current Gain ($I_C = -2.0$ mAdc, $V_{CE} = -5.0$ Vdc, $f = 1.0$ kHz)	h _{fe}	200	-	400	-
Noise Figure (I_C = -0.2 mAdc, V_{CE} = -5.0 Vdc, R_S = 2.0 k Ω , f = 1.0 kHz, f = 200 Hz) Small–Signal Current Gain (I_C = -2.0 mAdc, V_{CE} = -5.0 Vdc, f = 1.0 kHz) 1. Pulse Test: Tp 300 s, Duty Cycle 2.0%.					

^{1.} Pulse Test: Tp 300 s, Duty Cycle 2.0%.



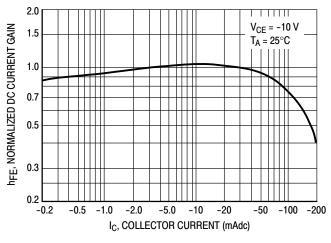


Figure 1. Normalized DC Current Gain

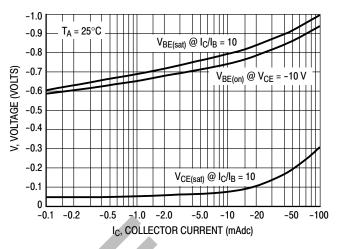


Figure 2. "Saturation" and "On" Voltages

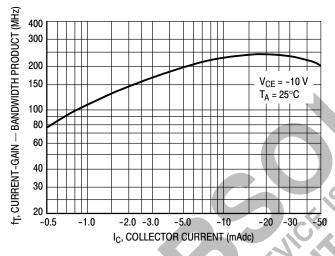


Figure 3. Current-Gain - Bandwidth Product

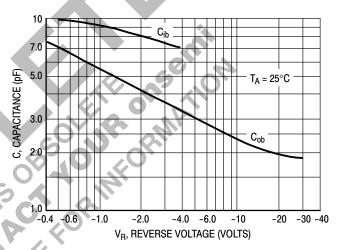


Figure 4. Capacitances

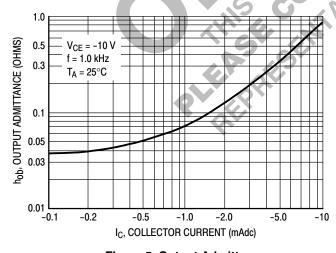


Figure 5. Output Admittance

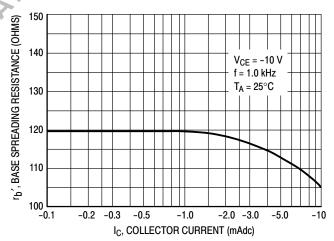
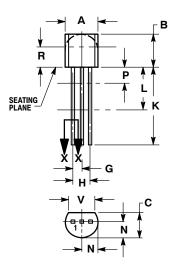


Figure 6. Base Spreading Resistance

BC212B

PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 **ISSUE AM**

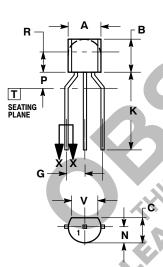


STRAIGHT LEAD **BULK PACK**



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982. CONTROLLING DIMENSION: INCH.
- CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
- LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	1	12.70	
L	0.250		6.35	<u></u>
N	0.080	0.105	2.04	2.66
Р		0.100		2.54
R	0.115		2.93	
V	0.135		3.43	



BENT LEAD TAPE & REEL AMMO PACK

SECTION X-X

NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. CONTROLLING DIMENSION: MILLIMETERS. CONTOUR OF PACKAGE BEYOND
- DIMENSION R IS UNCONTROLLED. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	MILLIMETERS		
DIM	MIN	MAX	
Α	4.45	5.20	
В	4.32	5.33	
С	3.18	4.19	
D	0.40	0.54	
G	2.40	2.80	
J	0.39	0.50	
K	12.70		
N	2.04	2.66	
P	1.50	4.00	
R	2.93		
V	3.43		

PIN 1. COLLECTOR

BASE

EMITTER

ON Semiconductor and 👊 are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice ON Semiconductor and "un" are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights or the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was penlinent reparding the design or manufacture of the part. SCILLC is an Equal to the second of the part of t associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA

Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free USA/Canada

Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910

Japan Customer Focus Center

Phone: 81-3-5773-3850

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

onsemi:

BC212B BC212BG BC212BRL1 BC212BRL1G BC214